

Features

- Optimized for 1.8V systems
 - As fast as 5.0 ns pin-to-pin delays
 - As low as 25 μ A quiescent current
- Industry's best 0.18 micron CMOS CPLD
 - Optimized architecture for effective logic synthesis
 - Multi-voltage I/O operation — 1.5V to 3.3V
- Available in multiple package options
 - 100-pin VQFP with 80 user I/O
 - 144-pin TQFP with 106 user I/O
 - 132-ball CP (0.5mm) BGA with 118 user I/O
 - 208-pin PQFP with 173 user I/O
 - 256-ball FT (1.0mm) BGA with 184 user I/O
- Advanced system features
 - Fastest in system programming
 - 1.8V ISP using IEEE 1532 (JTAG) interface
 - IEEE1149.1 JTAG Boundary Scan Test
 - Optional Schmitt-trigger input (per pin)
 - Unsurpassed low power management
 - Two separate output banks
 - Fast Zero Power™ (FZP) FZP 100% CMOS product term generation
 - DataGATE enable (DGE) signal control
 - Flexible clocking modes
 - Optional DualEDGE triggered registers
 - Clock divider (divide by 2,4,6,8,10,12,14,16)
 - CoolCLOCK
 - Global signal options with macrocell control
 - Multiple global clocks with phase selection per macrocell
 - Multiple global output enables
 - Global set/reset
 - Advanced design security
 - Open-drain output option for Wired-OR and LED drive
 - Optional bus-hold, 3-state or weak pullup on selected I/O pins
 - Optional configurable grounds on unused I/Os
 - Mixed I/O voltages compatible with 1.5V, 1.8V, 2.5V, and 3.3V logic levels
 - SSTL2-1, SSTL3-1, and HSTL-1 I/O compatibility
 - Hot pluggable

Refer to the CoolRunner™-II family data sheet for architecture description.

Description

The CoolRunner-II 256-macrocell device is designed for both high performance and low power applications. This lends power savings to high-end communication equipment and high speed to battery operated devices. Due to the low power stand-by and dynamic operation, overall system reliability is improved.

This device consists of sixteen Function Blocks inter-connected by a low power Advanced Interconnect Matrix (AIM). The AIM feeds 40 true and complement inputs to each Function Block. The Function Blocks consist of a 40 by 56 P-term PLA and 16 macrocells which contain numerous configuration bits that allow for combinational or registered modes of operation.

Additionally, these registers can be globally reset or preset and configured as a D or T flip-flop or as a D latch. There are also multiple clock signals, both global and local product term types, configured on a per macrocell basis. Output pin configurations include slew rate limit, bus hold, pull-up, open drain and programmable grounds. A Schmitt-trigger input is available on a per input pin basis. In addition to storing macrocell output states, the macrocell registers may be configured as "fast input" registers to store signals directly from input pins.

Clocking is available on a global or Function Block basis. Three global clocks are available for all Function Blocks as a synchronous clock source. Macrocell registers can be individually configured to power up to the zero or one state. A global set/reset control line is also available to asynchronously set or reset selected registers during operation. Additional local clock, synchronous clock-enable, asynchronous set/reset and output enable signals can be formed using product terms on a per-macrocell or per-Function Block basis.

A DualEDGE flip-flop feature is also available on a per macrocell basis. This feature allows high performance synchronous operation based on lower frequency clocking to help reduce the total power consumption of the device.

Circuitry has also been included to divide one externally supplied global clock (GCK2) by eight different selections. This yields divide by even and odd clock frequencies.

The use of the clock divide (division by 2) and DualEDGE flip-flop gives the resultant CoolCLOCK feature.

DataGATE is a method to selectively disable inputs of the CPLD that are not of interest during certain points in time.

By mapping a signal to the DataGATE function, lower power can be achieved due to reduction in signal switching.

Another feature that eases voltage translation is output banking. Two output banks are available on the CoolRunner-II 256-macrocell device that permits easy interfacing to 3.3V, 2.5V, 1.8V, and 1.5V devices.

The CoolRunner-II 256-macrocell CPLD is I/O compatible with standard LVTTTL and LVC MOS18, LVC MOS25, and LVC MOS33 (see Table 1). This device is also 1.5V I/O compatible with the use of Schmitt-trigger inputs.

Fast Zero Power Design Technology

Xilinx CoolRunner-II CPLDs are fabricated on a 0.18 micron process technology which is derived from leading edge FPGA product development. CoolRunner-II CPLDs employ Fast Zero Power™ (FZP), a design technique that makes use of CMOS technology in both the fabrication and design methodology. FZP design technology employs a cascade of CMOS gates to implement sum of products instead of traditional sense amplifier methodology. Due to this technology, Xilinx CoolRunner-II CPLDs achieve both high-performance and low power operation.

Supported I/O Standards

The CoolRunner-II 256 macrocell features both LVCMOS and LVTTTL I/O implementations. See Table 1 for I/O standard voltages. The LVTTTL I/O standard is a general purpose EIA/JEDEC standard for 3.3V applications that use an LVTTTL input buffer and Push-Pull output buffer. The LVCMOS standard is used in 3.3V, 2.5V, 1.8V applications. CoolRunner-II CPLDs are also 1.5V I/O compatible with the use of Schmitt-trigger inputs.

Table 1: I/O Standards for XC2C256

I/O Types	Output V_{CCIO}	Input V_{CCIO}	Input V_{REF}	Board Termination Voltage V_{TT}
LVTTTL	3.3	3.3	N/A	N/A
LVC MOS33	3.3	3.3	N/A	N/A
LVC MOS25	2.5	2.5	N/A	N/A
LVC MOS18	1.8	1.8	N/A	N/A
1.5V I/O	1.5	1.5	N/A	N/A
HSTL-1	1.5	1.5	0.75	0.75
SSTL2-1	2.5	2.5	1.25	1.25
SSTL3-1	3.3	3.3	1.5	1.5

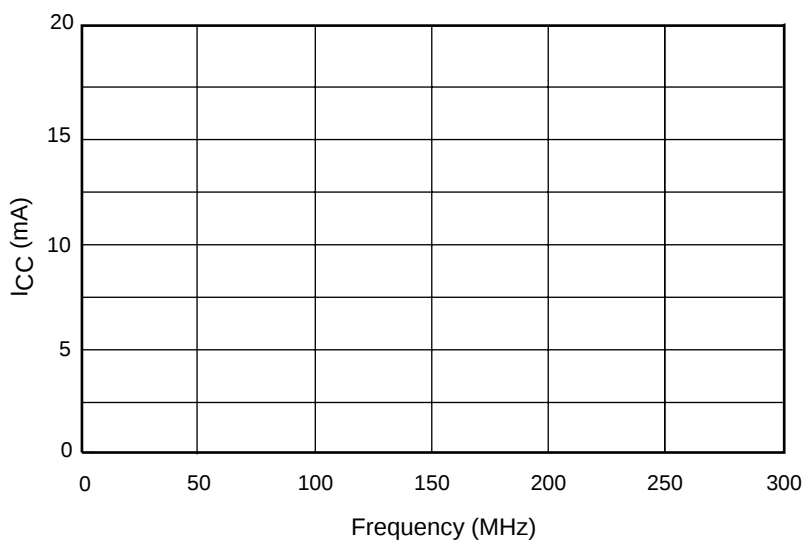


Figure 1: I_{CC} vs Frequency

Table 2: I_{CC} vs Frequency (LVCMOS 1.8V $T_A = 25^\circ\text{C}$)⁽¹⁾

	Frequency (MHz)										
	0	25	50	75	100	150	175	200	225	250	270
Typical -6, -7.5 I_{CC} (mA)											
Typical -5 I_{CC} (mA)											

Notes:

- 16-bit up/down, resettable binary counter (one counter per function block).

Absolute Maximum Ratings

Symbol	Description	Value	Units
V_{CC}	Supply voltage relative to ground	-0.5 to 2.0	V
V_{CCIO}	Supply voltage for output drivers	-0.5 to 4.0	V
V_{JTAG}	JTAG input voltage limits	-0.5 to 4.0	V
V_{AUX}	JTAG input supply voltage	-0.5 to 4.0	V
V_{IN}	Input voltage relative to ground ⁽¹⁾	-0.5 to 4.0	V
V_{TS}	Voltage applied to 3-state output ⁽¹⁾	-0.5 to 4.0	V
T_{STG}	Storage Temperature (ambient)	-65 to +150	°C
T_{SOL}	Maximum Soldering temperature (10s @ 1/16in. = 1.5mm)	+260	°C
T_J	Junction Temperature	+150	°C

Notes:

- Maximum DC undershoot below GND must be limited to either 0.5V or 10 mA, whichever is easiest to achieve. During transitions, the device pins may undershoot to -2.0V or overshoot to +4.5V, provided this over or undershoot lasts less than 10 ns and with the forcing current being limited to 200 mA.

Recommended Operating Conditions

Symbol	Parameter		Min	Max	Units
V _{CC}	Supply voltage for internal logic and input buffers	Commercial T _A = 0°C to +70°C	1.7	1.9	V
		Industrial T _A = −40°C to +85°C	1.7	1.9	V
V _{CCIO}	Supply voltage for output drivers @ 3.3V operation		3.0	3.6	V
	Supply voltage for output drivers @ 2.5V operation		2.3	2.7	V
	Supply voltage for output drivers @ 1.8V operation		1.7	1.9	V
	Supply voltage for output drivers @ 1.5V operation		1.4	1.6	V
V _{AUX}	JTAG programming		1.7	3.6	V

DC Electrical Characteristics (Over Recommended Operating Conditions)

Symbol	Parameter	Test Conditions	Min.	Max.	Units
I_{CCSB}	Standby current (-6, -7.5)	$V_{CC} = 1.9\text{V}$, $V_{CCIO} = 3.6\text{V}$	-	100	μA
I_{CCSB}	Standby current (-5)	$V_{CC} = 1.9\text{V}$, $V_{CCIO} = 3.6\text{V}$			mA
I_{CC}	Dynamic current (-6, -7.5)	$f = 1\text{ MHz}$			mA
		$f = 50\text{ MHz}$			mA
I_{CC}	Dynamic current (-5)	$f = 1\text{ MHz}$			mA
		$f = 50\text{ MHz}$			mA
C_{JTAG}	JTAG input capacitance	$f = 1\text{ MHz}$			pF
C_{CLK}	Global clock input capacitance	$f = 1\text{ MHz}$			pF
C_{IO}	I/O capacitance	$f = 1\text{ MHz}$			pF

LVC MOS 3.3V DC Voltage Specifications

Symbol	Parameter	Test Conditions	Min.	Max.	Units
V_{CCIO}	Input source voltage		3.0	3.6	V
V_{IH}	High level input voltage		2	$V_{CCIO} + 0.3V$	V
V_{IL}	Low level input voltage		-0.3	0.8	V
V_{OH}	High level output voltage	$I_{OH} = -8\text{ mA}, V_{CCIO} = 3V$	$V_{CCIO} - 0.4V$	-	V
		$I_{OH} = -0.1\text{ mA}, V_{CCIO} = 3V$	$V_{CCIO} - 0.2V$	-	V
V_{OL}	Low level output voltage	$I_{OL} = 8\text{ mA}, V_{CCIO} = 3V$	-	0.4	V
		$I_{OL} = 0.1\text{ mA}, V_{CCIO} = 3V$	-	0.2	V
I_{IL}	Input leakage current	$V_{IN} = 0V$ or V_{CCIO} to 3.9V	-10	10	μA
I_{IH}	I/O High-Z leakage	$V_{IN} = 0V$ or V_{CCIO} to 3.9V	-10	10	μA
C_{JTAG}	JTAG input capacitance	$f = 1\text{ MHz}$			pF
C_{CLK}	Global clock input capacitance	$f = 1\text{ MHz}$			pF
C_{IO}	I/O capacitance	$f = 1\text{ MHz}$			pF

LVC MOS 2.5V DC Voltage Specifications

Symbol	Parameter	Test Conditions	Min.	Max.	Units
V_{CCIO}	Input source voltage		2.3	2.7	V
V_{IH}	High level input voltage		1.7	3.9	V
V_{IL}	Low level input voltage		-0.3	0.7	V
V_{OH}	High level output voltage	$I_{OH} = -8\text{ mA}, V_{CCIO} = 2.3V$	$V_{CCIO} - 0.4V$	-	V
		$I_{OH} = -0.1\text{ mA}, V_{CCIO} = 2.3V$	$V_{CCIO} - 0.2V$	-	V
V_{OL}	Low level output voltage	$I_{OL} = 8\text{ mA}, V_{CCIO} = 2.3V$	-	0.4	V
		$I_{OL} = 0.1\text{ mA}, V_{CCIO} = 2.3V$	-	0.2	V
I_{IL}	Input leakage current	$V_{IN} = 0V$ or V_{CCIO} to 3.9V	-10	10	μA
I_{IH}	I/O High-Z leakage	$V_{IN} = 0V$ or V_{CCIO} to 3.9V	-10	10	μA
C_{JTAG}	JTAG input capacitance	$f = 1\text{ MHz}$			pF
C_{CLK}	Global clock input capacitance	$f = 1\text{ MHz}$			pF
C_{IO}	I/O capacitance	$f = 1\text{ MHz}$			pF

LVC MOS 1.8V DC Voltage Specifications

Symbol	Parameter	Test Conditions	Min.	Max.	Units
V_{CCIO}	Input source voltage		1.7	1.9	V
V_{IH}	High level input voltage		$0.7 \times V_{CCIO}$	3.9	V
V_{IL}	Low level input voltage		-0.3	$0.2 \times V_{CCIO}$	V
V_{OH}	High level output voltage	$I_{OH} = -8 \text{ mA}$, $V_{CCIO} = 1.7\text{V}$	$V_{CCIO} - 0.45$	-	V
		$I_{OH} = -0.1 \text{ mA}$, $V_{CCIO} = 1.7\text{V}$	$V_{CCIO} - 0.2$	-	V
V_{OL}	Low level output voltage	$I_{OL} = 8 \text{ mA}$, $V_{CCIO} = 1.7\text{V}$	-	0.45	V
		$I_{OL} = 0.1 \text{ mA}$, $V_{CCIO} = 1.7\text{V}$	-	0.2	V
I_{IL}	Input leakage current	$V_{IN} = 0$ or V_{CCIO} to 3.9V	-10	10	μA
I_{IH}	I/O High-Z leakage	$V_{IN} = 0$ or V_{CCIO} to 3.9V	-10	10	μA
C_{JTAG}	JTAG input capacitance	$f = 1 \text{ MHz}$			pF
C_{CLK}	Global clock input capacitance	$f = 1 \text{ MHz}$			pF
C_{IO}	I/O capacitance	$f = 1 \text{ MHz}$			pF

1.5V DC Voltage Specifications⁽¹⁾

Symbol	Parameter	Test Conditions	Min.	Max.	Units
V_{CCIO}	Input source voltage		1.4	1.6	V
V_{IH}	High level input voltage		$0.7 \times V_{CCIO}$	3.9	V
V_{IL}	Low level input voltage		-0.3	0.3	V
V_{OH}	High level output voltage	$I_{OH} = -8 \text{ mA}$, $V_{CCIO} = 1.4\text{V}$	$V_{CCIO} - 0.45$	-	V
		$I_{OH} = -0.1 \text{ mA}$, $V_{CCIO} = 1.4\text{V}$	$V_{CCIO} - 0.2$	-	V
V_{OL}	Low level output voltage	$I_{OL} = 8 \text{ mA}$, $V_{CCIO} = 1.4\text{V}$	-	0.4	V
		$I_{OL} = 0.1 \text{ mA}$, $V_{CCIO} = 1.4\text{V}$	-	0.2	V
I_{IL}	Input leakage current	$V_{IN} = 0$ or V_{CCIO} to 3.9V	-10	10	μA
I_{IH}	I/O High-Z leakage	$V_{IN} = 0$ or V_{CCIO} to 3.9V	-10	10	μA
C_{JTAG}	JTAG input capacitance	$f = 1 \text{ MHz}$			pF
C_{CLK}	Global clock input capacitance	$f = 1 \text{ MHz}$			pF
C_{IO}	I/O capacitance	$f = 1 \text{ MHz}$			pF

Notes:

1. Hysteresis used on 1.5V inputs.

AC Electrical Characteristics Over Recommended Operating Conditions

Symbol	Parameter	-5		-6		-7		Units
		Min.	Max.	Min.	Max.	Min.	Max.	
T_{PD1}	Propagation delay single p-term	-	4.7	-	5.6	-	6.7	ns
T_{PD2}	Propagation delay OR array	-	5.0	-	6.0	-	7.5	ns
T_{SUF}	Fast input register p-term clock setup time	1.8	-	2.0	-	2.3	-	ns
T_{SU1}	Setup time fast (single p-term)	1.9	-	2.4	-	2.5	-	ns
T_{SU2}	Setup time (OR array)	2.2	-	2.8	-	3.3	-	ns
T_{HF}	Fast input register hold time	0	-	0	-	0	-	ns
T_H	P-term hold time	0	-	0	-	0	-	ns
T_{CO}	Clock to output	-	3.8	-	4.5	-	6.0	ns
$F_{TOGGLE}^{(1)}$	Internal toggle rate	-	416	-	250	-	168	MHz
$F_{SYSTEM1}^{(2)}$	Maximum system frequency	-	238	-	213	-	159	MHz
$F_{SYSTEM2}^{(2)}$	Maximum system frequency	-	222	-	196	-	141	MHz
$F_{EXT1}^{(3)}$	Maximum external frequency	-	175	-	145	-	118	MHz
$F_{EXT2}^{(3)}$	Maximum external frequency	-	167	-	137	-	108	MHz
T_{PSUF}	Fast input register p-term clock setup time	1.0	-	0.9	-	1.5	-	ns
T_{PSU1}	P-term clock setup time (single p-term)	1.1	-	1.3	-	1.7	-	ns
T_{PSU2}	P-term clock setup time (OR array)	1.4	-	1.7	-	2.5	-	ns
T_{PHF}	Fast input register p-term clock hold time	0.5	-	0.9	-	0.7	-	ns
T_{PH}	P-term clock hold	0.4	-	0.5	-	0.5	-	ns
T_{PCO}	P-term clock to output	-	4.6	-	5.6	-	6.8	ns
T_{OE}/T_{OD}	Global OE to output enable/disable	-	4.8	-	5.6	-	7.0	ns
T_{POE}/T_{POD}	P-term OE to output enable/disable	-	5.4	-	6.4	-	7.3	ns
T_{MOE}/T_{MOD}	Macrocell driven OE to output enable/disable	-	6.2	-	7.2	-	9.2	ns
T_{PAO}	P-term set/reset to output valid	-	6.4	-	7.4	-	9.1	ns
T_{AO}	Global set/reset to output valid	-	6.5	-	7.3	-	9.3	ns
T_{SUEC}	Register clock enable setup time	2.0	-	2.5	-	2.6	-	ns
T_{HEC}	Register clock enable hold time	0	-	0	-	0	-	ns
T_{CW}	Global clock pulse width High or Low	1.2	-	2.0	-	3.0	-	ns
T_{PCW}	P-term pulse width High or Low	5.0	-	6.0	-	7.5	-	ns
T_{DGSU}	Set-up before DataGATE latch assertion	6.0	-	7.0	-	9.0	-	ns
T_{DGHO}	Hold to DataGATE latch assertion	6.0	-	7.0	-	9.0	-	ns
T_{DGR}	DataGATE recovery to new data	-	6.0	-	7.0	-	9.0	ns
T_{DGW}	DataGATE high pulse width	2.0	-	2.5	-	4.0	-	ns
T_{CDRSU}	CDRST setup time before falling edge GCLK2	1.0	-	1.3	-	2.0	-	ns
T_{CDRHO}	Hold time CDRST after falling edge GCLK2	0	-	0	-	0	-	ns
T_{CONFIG}	Configuration time							μ s

Notes:

- F_{TOGGLE} ($1/2 \cdot T_{CW}$) is the maximum frequency of a dual edge triggered T flip-flop with output enabled.
- $F_{SYSTEM1}$ ($1/T_{CYCLE}$) is the internal operating frequency for a device fully populated with 16-bit resettable binary counter through one p-term per macrocell while $F_{SYSTEM2}$ is through the OR array (one counter per function block).
- F_{EXT1} ($1/T_{SU2} + T_{CO}$) is the maximum external frequency using one p-term while F_{EXT2} is through the OR array.

Internal Timing Parameters

Symbol	Parameter ⁽¹⁾	-5		-6		-7		Units
		Min.	Max.	Min.	Max.	Min.	Max.	
Buffer Delays								
T _{IN}	Input buffer delay	-	1.9	-	2.3	-	2.4	ns
T _{FIN}	Fast data register input delay	-	2.2	-	2.4	-	3.0	ns
T _{GCK}	Global Clock buffer delay	-	1.6	-	1.8	-	2.5	ns
T _{GSR}	Global set/reset buffer delay	-	2.5	-	2.8	-	3.5	ns
T _{GTS}	Global 3-state buffer delay	-	1.8	-	2.1	-	3.0	ns
T _{OUT}	Output buffer delay	-	2.0	-	2.3	-	2.8	ns
T _{EN}	Output buffer enable/disable delay	-	3.0	-	3.5	-	4.0	ns
P-term Delays								
T _{CT}	Control term delay	-	0.5	-	0.6	-	0.9	ns
T _{LOGI1}	Single P-term delay adder	-	0.4	-	0.5	-	0.8	ns
T _{LOGI2}	Multiple P-term delay adder	-	0.3	-	0.4	-	0.8	ns
Macrocell Delay								
T _{PDI}	Input to output valid	-	0.4	-	0.5	-	0.7	ns
T _{SUI}	Setup before clock	1.2	-	1.4	-	1.8	-	ns
T _{HI}	Hold after clock	0	-	0	-	0	-	ns
T _{ECSU}	Enable clock setup time	1.2	-	1.4	-	1.8	-	ns
T _{ECHO}	Enable clock hold time	0	-	0	-	0	-	ns
T _{COI}	Clock to output valid	-	0.2	-	0.4	-	0.7	ns
T _{AOI}	Set/reset to output valid	-	2.0	-	2.2	-	3.0	ns
T _{CDBL}	Clock doubler delay	-	0	-	0	-	0	ns
Feedback Delays								
T _F	Feedback delay	-	2.4	-	2.4	-	3.0	ns
T _{OEM}	Macrocell to global OE delay	-	1.4	-	1.5	-	2.0	ns
I/O Standard Time Adder Delays 1.5V I/O								
T _{IN15}	Standard input adder	-	0	-	0	-	0	ns
T _{HYS15}	Hysteresis input adder	-	2.0	-	3.0	-	4.0	ns
T _{OUT15}	Output adder	-	0	-	0	-	0	ns
T _{SLEW15}	Output slew rate adder	-	2.0	-	3.0	-	4.0	ns
I/O Standard Time Adder Delays 1.8V CMOS								
T _{IN18}	Standard input adder	-	0	-	0	-	0	ns
T _{HYS18}	Hysteresis input adder	-	2.0	-	3.0	-	4.0	ns
T _{OUT18}	Output adder	-	0	-	0	-	0	ns
T _{SLEW}	Output slew rate adder	-	2.0	-	3.0	-	4.0	ns

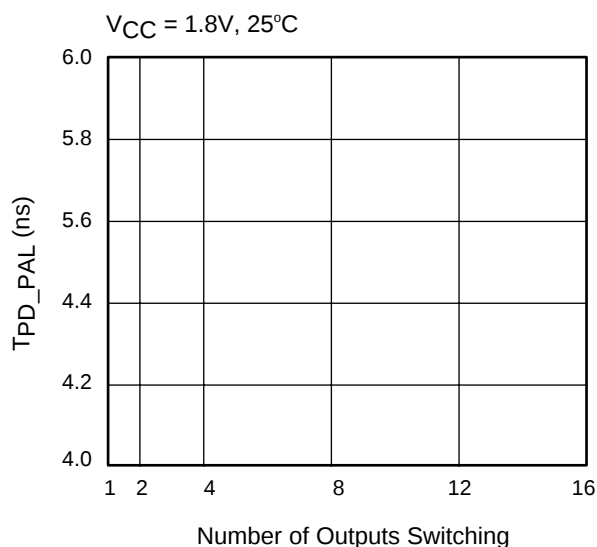
Internal Timing Parameters (Continued)

Symbol	Parameter ⁽¹⁾	-5		-6		-7		Units
		Min.	Max.	Min.	Max.	Min.	Max.	
I/O Standard Time Adder Delays 2.5V CMOS								
T _{IN25}	Standard input adder	-	0.5	-	0.8	-	1.0	ns
T _{HYS25}	Hysteresis input adder	-	1.5	-	2.5	-	3.0	ns
T _{OUT25}	Output adder	-	1.5	-	2.5	-	3.0	ns
T _{SLEW25}	Output slew rate adder	-	2.0	-	3.0	-	4.0	ns
I/O Standard Time Adder Delays 3.3V CMOS/TTL								
T _{IN33}	Standard input adder	-	0.7	-	1.0	-	2.0	ns
T _{HYS33}	Hysteresis input adder	-	1.0	-	2.0	-	3.0	ns
T _{OUT33}	Output adder	-	1.0	-	2.0	-	3.0	ns
T _{SLEW33}	Output slew rate adder	-	2.0	-	3.0	-	4.0	ns
I/O Standard Time Adder Delays HSTL, SSTL								
SSTL2-1	Input adder to TIN, TFIN, TGCK, TGSR,TGTS	-	1.5	-	1.8	-	2.5	ns
	Output adder to TOUT	-	0	-	0	-	0	ns
SSTL3-1	Input adder to TIN, TFIN, TGCK, TGSR,TGTS	-	1.5	-	1.8	-	2.5	ns
	Output adder to TOUT	-	0	-	0	-	0	ns
HSTL-1	Input adder to TIN, TFIN, TGCK, TGSR,TGTS	-	1.5	-	1.8	-	2.5	ns
	Output adder to TOUT	-	0	-	0	-	0	ns

Notes:

1. 1.5 ns input pin signal rise/fall.

Switching Characteristics



DS092_09_121501

Pin Descriptions

Function Block	Macro-cell	VQ100	CP132	TQ144	PQ208	FT256	I/O Bank
1	1	-	-	-	2	B3	2
1	2	-	-	-	208	B4	2
1(GSR)	3	99	A3	143	206	C4	2
1	4	-	-	142	205	A2	2
1	5	-	-	-	203	A3	2
1	6	97	B4	140	202	A4	2
1	7	-	-	-	-	-	-
1	8	-	-	-	-	-	-
1	9	-	-	-	-	-	-
1	10	-	-	-	-	-	-
1	11	-	-	-	-	-	-
1	12	96	-	139	201	B5	2
1	13	95	-	138	200	A5	2
1	14	94	A4	137	199	E8	2
1	15	-	-	-	198	B6	2
1	16	-	C5	-	197	C7	2
2(GTS2)	1	1	A1	2	3	D3	2
2	2	-	-	-	4	C3	2
2(GTS3)	3	2	B2	3	5	E3	2
2	4	-	B1	4	6	B2	2
2(GTS0)	5	3	C3	5	7	D4	2
2	6	-	-	-	8	D2	2
2	7	-	-	-	-	-	-
2	8	-	-	-	-	-	-
2	9	-	-	-	-	-	-
2	10	-	-	-	-	-	-
2	11	-	-	-	-	-	-
2(GTS1)	12	4	C2	6	9	E5	2
2	13	-	C1	7	10	B1	2
2	14	6	D2	9	12	E4	2
2	15	7	-	10	14	C1	2
2	16	-	D1	-	-	E2	2

Pin Descriptions (Continued)

Function Block	Macro-cell	VQ100	CP132	TQ144	PQ208	FT256	I/O Bank
3	1	-	-	136	196	A6	2
3	2	-	B5	135	195	D7	2
3	3	-	-	134	194	B7	2
3	4	-	A5	-	193	E9	2
3	5	93	-	133	192	A7	2
3	6		C6		191	D8	2
3	7	-	-	-	-	-	-
3	8	-	-	-	-	-	-
3	9	-	-	-	-	-	-
3	10	-	-	-	-	-	-
3	11	-	-	-	-	-	-
3	12	92	-	-	189	B8	2
3	13	-	B6	-	188	C8	2
3	14	91	A6	132	187	A8	2
3	15	-	C7	-	186	E11	2
3	16	90	B7	131	185	E10	2
4	1	8	E3	11	15	F2	2
4	2	9	-	12	16	F3	2
4	3	10	E2	13	17	G4	2
4	4	-	E1	14	18	G3	2
4	5	11	F3	15	19	F5	2
4	6	12	F2	16	20	G5	2
4	7	-	-	-	-	-	-
4	8	-	-	-	-	-	-
4	9	-	-	-	-	-	-
4	10	-	-	-	-	-	-
4	11	-	-	-	-	-	-
4	12	-	F1	17	21	H2	2
4	13	13	G1	-	22	H4	2
4	14	-	-	18	23	H3	2
4	15	-	-	-	-	H1	2
4	16	-	-	-	25	H5	2

Pin Descriptions (Continued)

Function Block	Macro-cell	VQ100	CP132	TQ144	PQ208	FT256	I/O Bank
5	1	-	L3	-	49	R1	1
5	2	-	-	33	48	N4	1
5	3	-	-	-	47	N2	1
5(GCK1)	4	23	L2	32	46	M3	1
5	5		L1	31	45	P1	1
5(GCK0)	6	22	K3	30	44	M2	1
5	7	-	-	-	-	-	-
5	8	-	-	-	-	-	-
5	9	-	-	-	-	-	-
5	10	-	-	-	-	-	-
5	11	-	-	-	-	-	-
5	12	-	-	-	43	L3	1
5	13	-	-	-	41	N1	1
5	14	-	-	28	40	L4	1
5	15	-	-	-	39	M1	1
5	16	-	K1	-	38	L5	1
6	1	-	M1	34	50	N3	1
6 (CDRST)	2	24	M2	35	51	P2	1
6	3	-	-	-	54	P4	1
6(GCK2)	4	27	N2	38	55	P5	1
6	5	-	-	-	56	R2	1
6	6	-	-	-	57	T1	1
6	7	-	-	-	-	-	-
6	8	-	-	-	-	-	-
6	9	-	-	-	-	-	-
6	10	-	-	-	-	-	-
6	11	-	-	-	-	-	-
6(DGE)	12	28	P2	39	58	T2	1
6	13	-	M3	40	60	N5	1
6	14	29	N3	41	61	R4	1
6	15	-	P3	42	62	M5	1
6	16	30	M4	43	63	R5	1

Pin Descriptions (Continued)

Function Block	Macro-cell	VQ100	CP132	TQ144	PQ208	FT256	I/O Bank
7	1	-	-	-	37	K4	1
7	2	-	-	-	36	L2	1
7	3	-	-	-	35	K3	1
7	4	-	-	-	34	L1	1
7	5	19	J2	26	32	K5	1
7	6	18	J1	25	31	K2	1
7	7	-	-	-	-	-	-
7	8	-	-	-	-	-	-
7	9	-	-	-	-	-	-
7	10	-	-	-	-	-	-
7	11	17	H3	24	30	J4	1
7	12	16	H2	23	29	K1	1
7	13	15	H1	22	28	J3	1
7	14	14	G3	21	27	J2	1
7	15	-	G2	20	-	J5	1
7	16	-	-	19	-	J1	1
8	1	-	N4	44	64	R6	1
8	2	-	-	45	65	N6	1
8	3	-	-	46	66	R3	1
8	4	-	-	-	67	M6	1
8	5	-	-	48	69	T3	1
8	6	32	-	49	70	P6	1
8	7	-	-	-	-	-	-
8	8	-	-	-	-	-	-
8	9	-	-	-	-	-	-
8	10	-	-	-	-	-	-
8	11	33	M5	50	71	T4	1
8	12	34	N5	51	72	P7	1
8	13	35	P5	52	73	T5	1
8	14	36	M6	-	74	N7	1
8	15	37	N6	-	75	R7	1
8	16	-	-	-	76	M7	1

Pin Descriptions (Continued)

Function Block	Macro-cell	VQ100	CP132	TQ144	PQ208	FT256	I/O Bank
9	1	78	C12	112	160	B13	2
9	2	79	B12	113	161	B14	2
9	3	-	-	-	162	C13	2
9	4	80	A12	114	163	A15	2
9	5				164	C12	2
9	6	81	C11	115	165	B12	2
9	7	-	-	-	-	-	-
9	8	-	-	-	-	-	-
9	9	-	-	-	-	-	-
9	10	-	-	-	-	-	-
9	11	-	-	-	166	D13	2
9	12	82	B11	116	167	A14	2
9	13	-	-	117	168	E13	2
9	14	-	A11	118	169	A13	2
9	15	-	-	119	170	C11	2
9	16	-	C10	-	171	A12	2
10	1	77	A13	111	159	A16	2
10	2	76	B13	110	158	B15	2
10	3	74	C13	107	155	C14	2
10	4	73	C14	106	154	G11	2
10	5	72	D12	105	153	B16	2
10	6	71	D13	104	152	D15	2
10	7	-	-	-	-	-	-
10	8	-	-	-	-	-	-
10	9	-	-	-	-	-	-
10	10	-	-	-	-	-	-
10	11				151	E14	2
10	12	70	D14	103	150	C16	2
10	13	-	-	-	149	F14	2
10	14	-	E12	102	148	F13	2
10	15	-	-	-	147	E15	2
10	16	-	E13	101	146	G13	2

Pin Descriptions (Continued)

Function Block	Macro-cell	VQ100	CP132	TQ144	PQ208	FT256	I/O Bank
11	1	-	B10	-	-	B11	2
11	2	-		-	173	D11	2
11	3	-	A10	-	174	A11	2
11	4	-	-	-	175	D10	2
11	5	-	C9	120	-	B10	2
11	6	-	-	121	-	E12	2
11	7	-	-	-	-	-	-
11	8	-	-	-	-	-	-
11	9	-	-	-	-	-	-
11	10	-	-	-	-	-	-
11	11	85	A8	124	178	F12	2
11	12	86	B8	125	179	B9	2
11	13	87	C8	126	180	C9	2
11	14	89	-	128	182	C10	2
11	15	-	-	129	183	A9	2
11	16	-	-	130	184	D9	2
12	1	-	-	-	145	F15	2
12	2	-	-	100	144	G14	2
12	3	-	-	-	143	E16	2
12	4	-	-	-	142	H12	2
12	5	-	F12	-	140	F16	2
12	6	-	F13	-	139	H16	2
12	7	-	-	-	-	-	-
12	8	-	-	-	-	-	-
12	9	-	-	-	-	-	-
12	10	-	-	-	-	-	-
12	11	68	F14	98	138	G15	2
12	12	-	G12	97	137	H13	2
12	13	67	G13	96	136	G16	2
12	14	66	-	95	135	H14	2
12	15	65	-	94	134	H15	2
12	16	-	-	-	-	J12	2

Pin Descriptions (Continued)

Function Block	Macro-cell	VQ100	CP132	TQ144	PQ208	FT256	I/O Bank
13	1	-	N13	75	107	R15	1
13	2	53	N14	76	108	T16	1
13	3	-	M12	77	109	N14	1
13	4	54	-	-	110	R16	1
13	5	-	M13	78	111	N15	1
13	6	55	-	79	112	M15	1
13	7	-	-	-	-	-	-
13	8	-	-	-	-	-	-
13	9	-	-	-	-	-	-
13	10	-	-	-	-	-	-
13	11	-	-	-	-	-	-
13	12	-	M14	80	113	M13	1
13	13	56	-	81	114	P16	1
13	14	-	L12	82	115	N16	1
13	15	-	-	-	116	L14	1
13	16	-	L13	-	117	M14	1
14	1	52	P14	74	106	P15	1
14	2	-	-	71	103	P14	1
14	3	50	P12	70	102	P13	1
14	4	-	M11	69	101	R13	1
14	5	49	N11	-	100	N13	1
14	6	-	P11	68	-	R14	1
14	7	-	-	-	-	-	-
14	8	-	-	-	-	-	-
14	9	-	-	-	-	-	-
14	10	-	-	-	-	-	-
14	11	-	-	-	-	-	-
14	12	-	-	-	99	T15	1
14	13	-	-	66	97	R12	1
14	14	46	P10	64	95	N11	1
14	15	44	-	-	-	M11	1
14	16	-	P9	61	91	N10	1

Pin Descriptions (Continued)

Function Block	Macro-cell	VQ100	CP132	TQ144	PQ208	FT256	I/O Bank
15	1	-	-	-	118	L15	1
15	2	-	L14	83	119	L13	1
15	3	-	-	-	120	M12	1
15	4	-	-	-	121	M16	1
15	5	-	-	-	122	K14	1
15	6	-	-	-	123	L16	1
15	7	-	-	-	-	-	-
15	8	-	-	-	-	-	-
15	9	-	-	-	-	-	-
15	10	-	-	-	-	-	-
15	11	58	K13	85	125	K15	1
15	12	59	K14	86	126	L12	1
15	13	60	J12	87	127	K16	1
15	14	61	J13	88	128	J14	1
15	15	63	H13	91	-	J15	1
15	16	64	H12	92	131	J13	1
16	1	-	-	-	90	P10	1
16	2	-	-	-	89	R10	1
16	3	-	M8	-	88	T10	1
16	4	-	-	-	87	R9	1
16	5	43	N8	60	86	N9	1
16	6	42	-	59	85	M8	1
16	7	-	-	-	-	-	-
16	8	-	-	-	-	-	-
16	9	-	-	-	-	-	-
16	10	-	-	-	-	-	-
16	11	41	P8	58	84	T8	1
16	12	40	M7	57	83	P8	1
16	13	39	N7	56	82	R8	1
16	14	-	-	-	80	T7	1
16	15	-	-	54	78	N8	1
16	16	-	P6	53	77	T6	1

Notes:

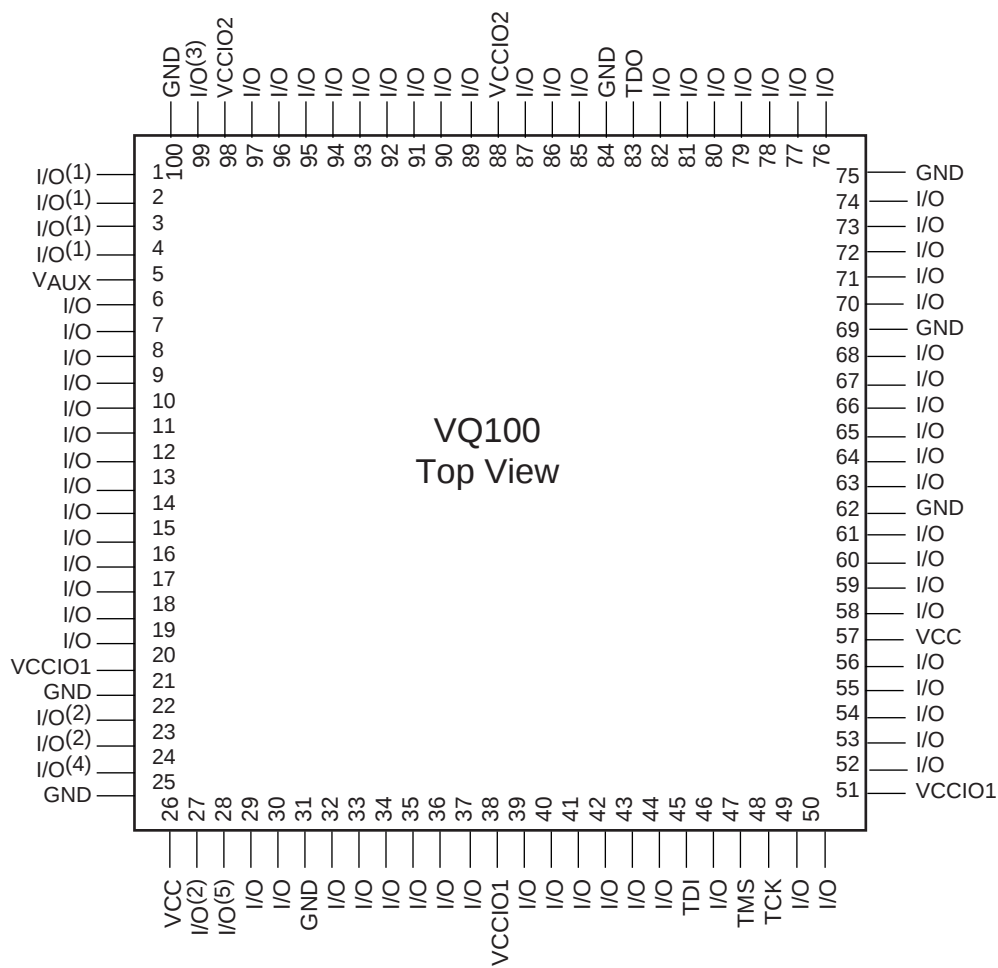
1. GTS = global output enable, GSR = global reset/set, GCK = global clock, CDRST = clock divide reset, DGE = DataGATE enable.

XC2C256 JTAG, Power/Ground, No Connect Pins and Total User I/O

Pin Type	VQ100	CP132	TQ144	PQ208	FT256
TCK	48	M10	67	98	P12
TDI	45	M9	63	94	R11
TDO	83	B9	122	176	A10
TMS	47	N10	65	96	N12
V _{AUX} (JTAG supply voltage)	5	D3	8	11	F4
Power internal (V _{CC})	26, 57	P1, K12, A2	1, 37, 84	1, 53, 124	P3, K13, D12, D5
Power Bank 1 I/O (V _{CCIO1})	20, 38, 51	J3, P7, G14, P13	27, 55, 73, 93	33, 59, 79, 92, 105, 132	J6, K6, L7, L8, J11, K11, L10, L9
Power Bank 2 I/O (V _{CCIO2})	88, 98	A14, C4, A7	109, 127, 141	26, 133, 157, 172, 181, 204	F7, F8, G6, H6, F10, F9, H11
Ground	21, 25, 31, 62, 69, 75, 84, 100	K2, N1, P4, N9, N12, J14, H14, E14, B14, A9, B3	29, 36, 47, 62, 72, 89, 90, 99, 108, 123, 144	13, 24, 42, 52, 68, 81, 93, 104, 129, 130, 141, 156, 177, 190, 207	F11, F6, G10, G7, G8, G9, H10, H7, H8, H9, J10, J7, J8, J9, K10, K7, K8, K9, L11, L6
No connects	-	-	-	-	A1, C2, E6, D1, E1, G2, F1, G1, M4, T9, P9, M9, M10, T11, T12, T13, P11, T14, J16, K12, D16, G12, C15, D14, D6, C6, E7, C5
Total user I/O	72	98	110	165	176

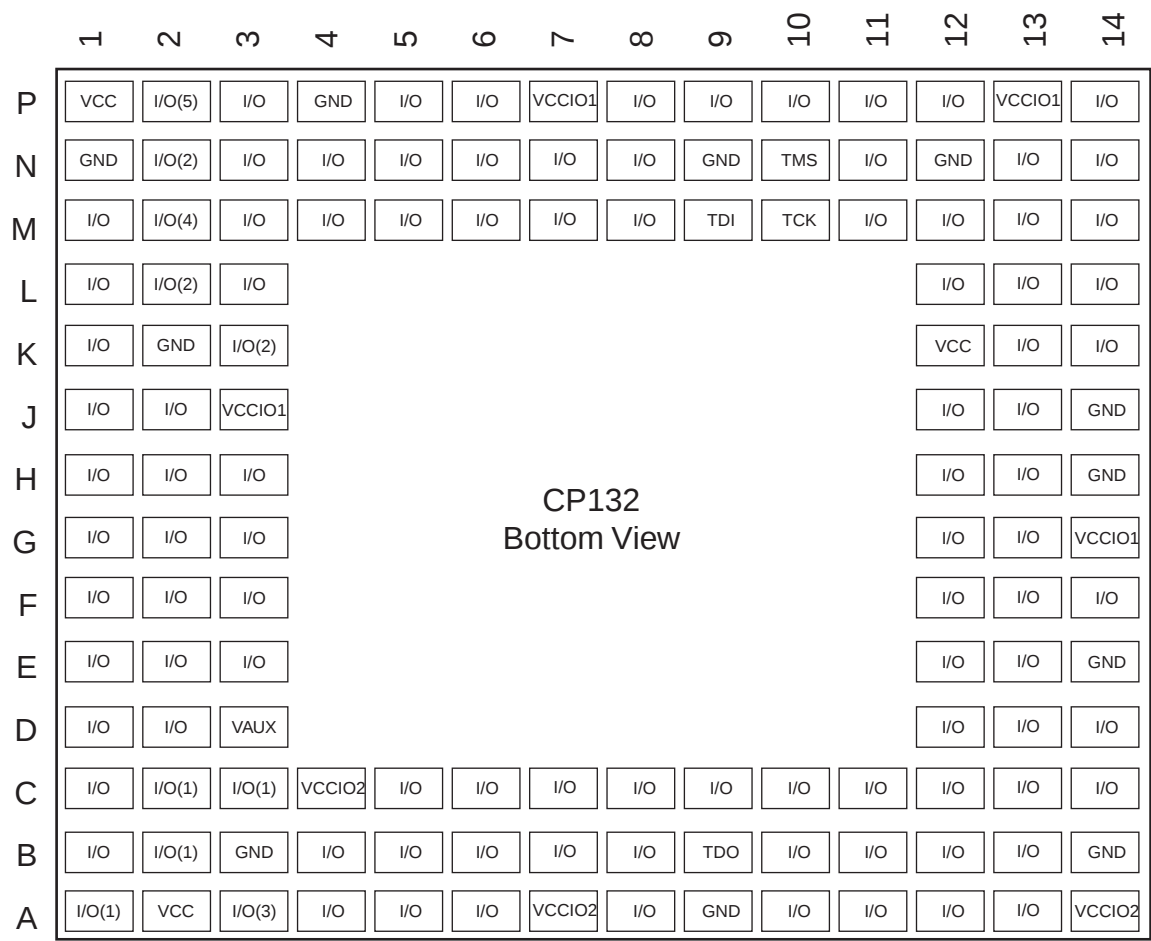
Ordering Information

Part Number	Pin/Ball Spacing	θ_{JA} (C/Watt)	θ_{JC} (C/Watt)	Package Type	Package Dimensions	I/O	Commercial (C) Industrial (I)
XC2C256-5VQ100	0.5mm	43.1	10.9	Very Thin Quad Flat Pack	14mm x 14mm	72	C
XC2C256-6VQ100	0.5mm	43.1	10.9	Very Thin Quad Flat Pack	14mm x 14mm	72	C
XC2C256-7VQ100	0.5mm	43.1	10.9	Very Thin Quad Flat Pack	14mm x 14mm	72	C
XC2C256-5CP132	0.5mm	65.0	15.0	Chip Scale Package	8mm x 8mm	98	C
XC2C256-6CP132	0.5mm	65.0	15.0	Chip Scale Package	8mm x 8mm	98	C
XC2C256-7CP132	0.5mm	65.0	15.0	Chip Scale Package	8mm x 8mm	98	C
XC2C256-5TQ144	0.5mm	37.2	7.2	Thin Quad Flat Pack	20mm x 20mm	110	C
XC2C256-6TQ144	0.5mm	37.2	7.2	Thin Quad Flat Pack	20mm x 20mm	110	C
XC2C256-7TQ144	0.5mm	37.2	15.0	Thin Quad Flat Pack	20mm x 20mm	110	C
XC2C256-5PQ208	0.5mm	36.9	9.7	Plastic Quad Flat Pack	28mm x 28mm	165	C
XC2C256-6PQ208	0.5mm	36.9	9.7	Plastic Quad Flat Pack	28mm x 28mm	165	C
XC2C256-7PQ208	0.5mm	36.9	9.7	Plastic Quad Flat Pack	28mm x 28mm	165	C
XC2C256-5FT256	1.0mm	34.6	6.1	Fine Pitch Thin BGA	17mm x 17mm	176	C
XC2C256-6FT256	1.0mm	34.6	6.1	Fine Pitch Thin BGA	17mm x 17mm	176	C
XC2C256-7FT256	1.0mm	34.6	6.1	Fine Pitch Thin BGA	17mm x 17mm	176	C
XC2C256-7VQ100	0.5mm	43.1	10.9	Very Thin Quad Flat Pack	14mm x 14mm	72	I
XC2C256-7CP132	0.5mm	65.0	15.0	Chip Scale Package	8mm x 8mm	98	I
XC2C256-7TQ144	0.5mm	37.2	7.2	Thin Quad Flat Pack	20mm x 20mm	110	I
XC2C256-7PQ208	0.5mm	36.9	9.7	Plastic Quad Flat Pack	28mm x 28mm	165	I
XC2C256-7FT256	1.0mm	34.6	6.1	Fine Pitch Thin BGA	17mm x 17mm	176	I



- (1) - Global Output Enable
- (2) - Global Clock
- (3) - Global Set/Reset
- (4) - Clock Divide Reset
- (5) - Data Gate

Figure 2: VQ100 Very Thin Quad Flat Pack



- (1) - Global Output Enable
- (2) - Global Clock
- (3) - Global Set/Reset
- (4) - Clock Divide Reset
- (5) - DataGATE Enable

Figure 3: CP132 Chip Scale Package

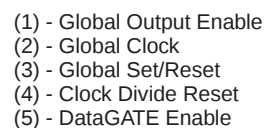
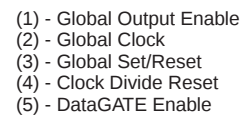


Figure 4: TQ144 Thin Quad Flat Pack



DS094 (v1.1) May 13, 2002
Advance Product Specification

	16	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1
A	I/O	I/O	I/O	I/O	I/O	I/O	TDO	I/O	I/O	I/O	I/O	I/O	I/O	I/O	I/O	NC
B	I/O	I/O	I/O	I/O	I/O	I/O	I/O	I/O	I/O	I/O	I/O	I/O	I/O	I/O	I/O	I/O
C	I/O	NC	I/O	I/O	I/O	I/O	I/O	I/O	I/O	I/O	NC	NC	I/O(3)	I/O	NC	I/O
D	NC	I/O	NC	I/O	VCC	I/O	I/O	I/O	I/O	I/O	NC	VCC	I/O(1)	I/O(1)	I/O	NC
E	I/O	I/O	I/O	I/O	I/O	I/O	I/O	I/O	I/O	NC	NC	I/O(1)	I/O	I/O(1)	I/O	NC
F	I/O	I/O	I/O	I/O	I/O	GND	VCCIO2	VCCIO2	VCCIO2	VCCIO2	GND	I/O	VAUX	I/O	I/O	NC
G	I/O	I/O	I/O	I/O	NC	I/O	GND	GND	GND	GND	VCCIO2	I/O	I/O	I/O	NC	NC
H	I/O	I/O	I/O	I/O	I/O	VCCIO2	GND	GND	GND	GND	VCCIO2	I/O	I/O	I/O	I/O	I/O
J	NC	I/O	I/O	I/O	I/O	VCCIO1	GND	GND	GND	GND	VCCIO1	I/O	I/O	I/O	I/O	I/O
K	I/O	I/O	I/O	VCC	NC	VCCIO1	GND	GND	GND	GND	VCCIO1	I/O	I/O	I/O	I/O	I/O
L	I/O	I/O	I/O	I/O	I/O	GND	VCCIO1	VCCIO1	VCCIO1	VCCIO1	GND	I/O	I/O	I/O	I/O	I/O
M	I/O	I/O	I/O	I/O	I/O	I/O	NC	NC	I/O	I/O	I/O	I/O	NC	I/O(2)	I/O(2)	I/O
N	I/O	I/O	I/O	I/O	TMS	I/O	I/O	I/O	I/O	I/O	I/O	I/O	I/O	I/O	I/O	I/O
P	I/O	I/O	I/O	I/O	TCK	NC	I/O	NC	I/O	I/O	I/O	I/O(2)	I/O	VCC	I/O(4)	I/O
R	I/O	I/O	I/O	I/O	I/O	TDI	I/O	I/O	I/O	I/O	I/O	I/O	I/O	I/O	I/O	I/O
T	I/O	I/O	NC	NC	NC	NC	I/O	NC	I/O	I/O	I/O	I/O	I/O	I/O	I/O(5)	I/O

FT256 Bottom View

- (1) - Global Output Enable
- (2) - Global Clock
- (3) - Global Set/Reset
- (4) - Clock Divide Reset
- (5) - DataGATE Enable

Figure 6: FT256 Fine Pitch Thin BGA

Revision History

The following table shows the revision history for this document.

Date	Version	Revision
05/09/02	1.0	Initial Xilinx release.
05/13/02	1.1	Updated AC Electrical Characteristics and added new parameters.